

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-20V	5.5Ω @ V _{GS} = -4.5V	-200mA
	7.5Ω @ V _{GS} = -2.5V	-170mA

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power-management applications.

Applications

- DC-DC converters
- Power-management functions

Features

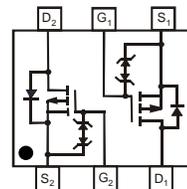
- Dual P-Channel MOSFET
- Low On-Resistance
 - 5.5Ω @ -4.5V
 - 7.5Ω @ -2.5V
 - 11.5Ω @ -1.8V
 - 17.5Ω @ -1.5V
- Very Low Gate Threshold Voltage V_{GS(TH)} < 1.15V
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

- Package: SOT963
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.0027 grams (Approximate)



Top View

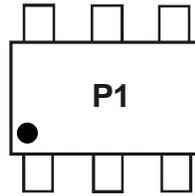


Internal Schematic

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP210DUDJ-7	SOT963	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information (Note 5)


P1 = Product Type Marking Code

Note: 5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	T _A = +25°C	-200
		T _A = +70°C	-150
Continuous Drain Current (Note 6) V _{GS} = -2.5V	I _D	T _A = +25°C	-170
		T _A = +70°C	-130
Pulsed Drain Current	I _{DM}	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P _D	330	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	377.16	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-100	nA	V _{DS} = -16V, V _{GS} = 0V
		—	—	-50	nA	V _{DS} = -5.0V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±5.0V, V _{DS} = 0V
		—	—	±1	μA	V _{GS} = ±8.0V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.45	—	-1.15	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{Ds(ON)}	—	—	5.5	Ω	V _{GS} = -4.5V, I _D = -100mA
		—	—	7.5		V _{GS} = -2.5V, I _D = -50mA
		—	—	11.5		V _{GS} = -1.8V, I _D = -20mA
		—	—	17.5		V _{GS} = -1.5V, I _D = -10mA
		—	20	—		V _{GS} = -1.2V, I _D = -1mA
Forward Transfer Admittance	Y _{fs}	—	200	—	mS	V _{DS} = -10V, I _D = -0.2A
Diode Forward Voltage (Note 7)	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	13.72	27.44	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	4.01	8.02	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.34	4.68	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{d(on)}	—	7.7	—	ns	V _{GS} = -4.5V, V _{DD} = -15V, I _D = -180mA, R _G = 2.0Ω
Rise Time	t _r	—	19.3	—		
Turn-Off Delay Time	t _{d(off)}	—	25.9	—		
Fall Time	t _f	—	31.5	—		

 Notes: 6. Device mounted on 1"x1" FR-4 substrate PCB, with minimum recommended pad layout, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

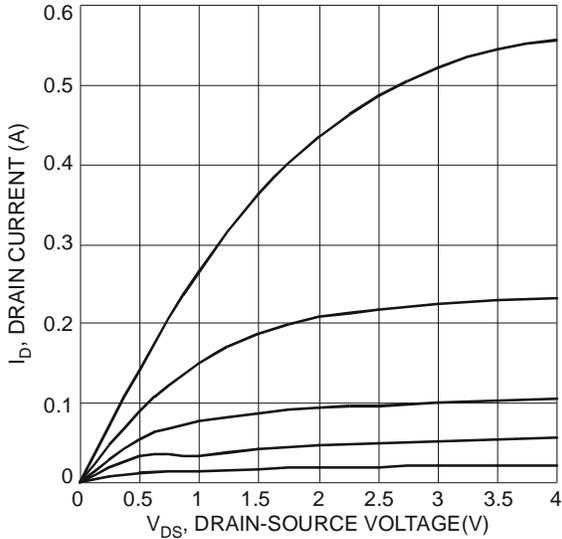


Fig. 1 Typical Output Characteristics

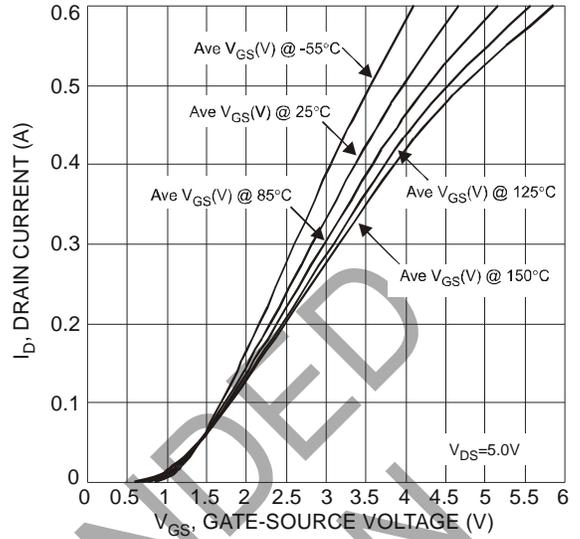


Fig. 2 Typical Transfer Characteristics

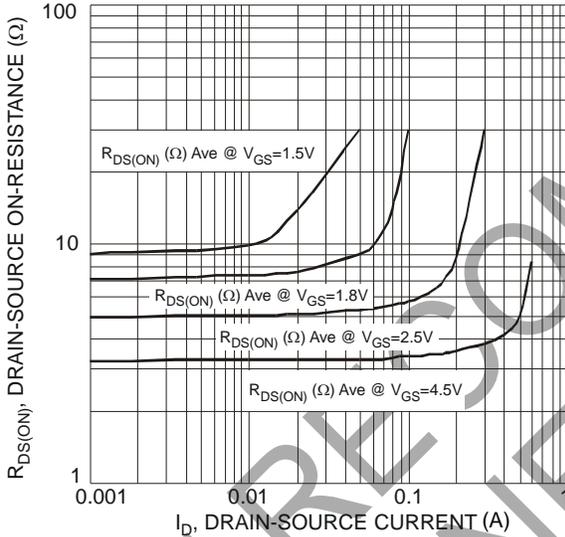


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

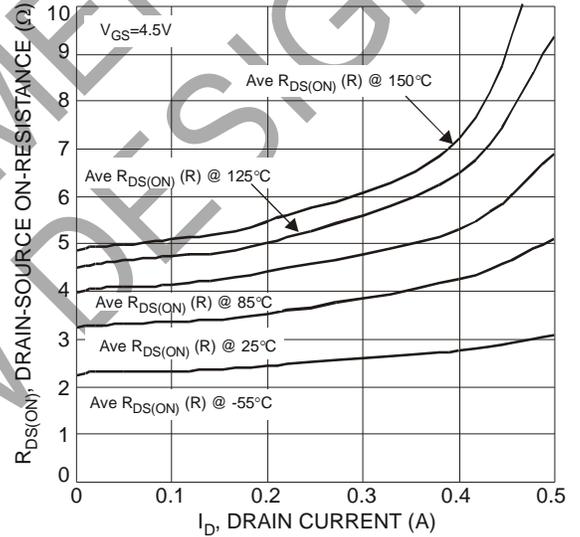


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

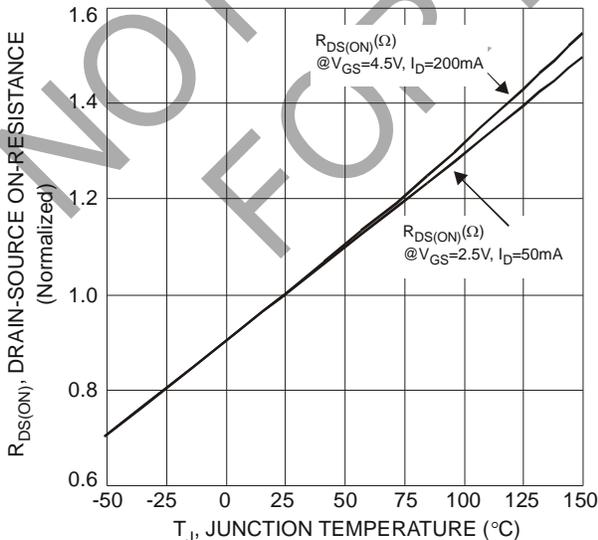


Fig. 5 On-Resistance Variation with Temperature

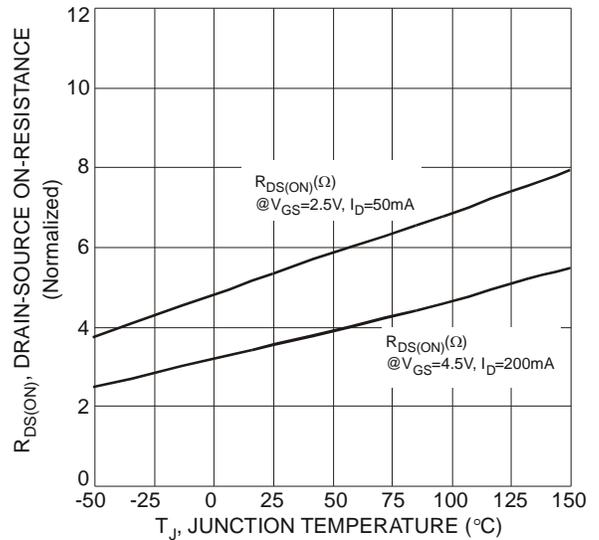


Fig. 6 On-Resistance vs. Temperature

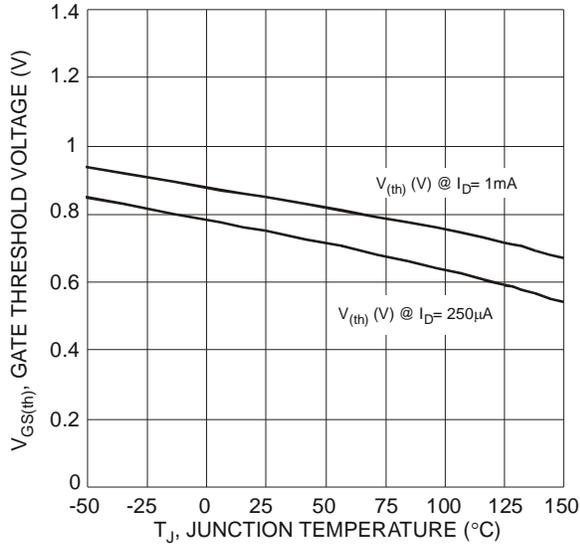


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

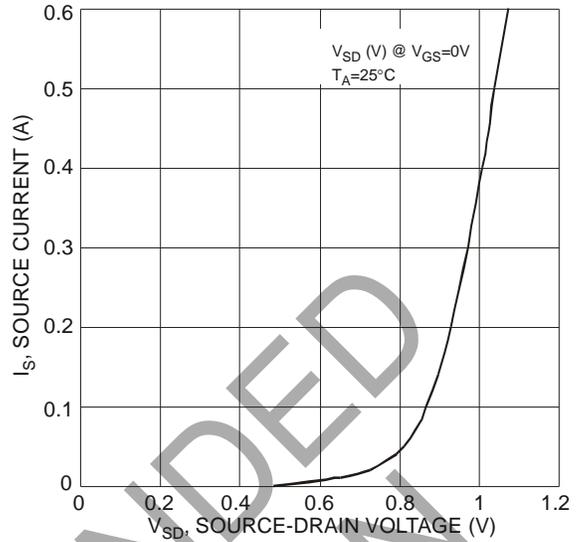


Fig. 8 Diode Forward Voltage vs. Current

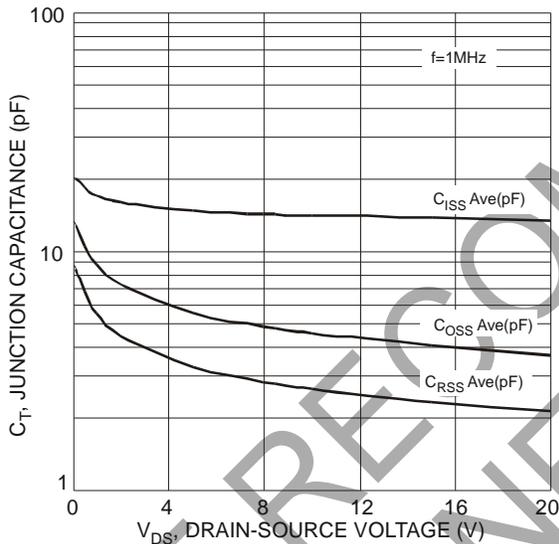


Fig. 9 Typical Junction Capacitance

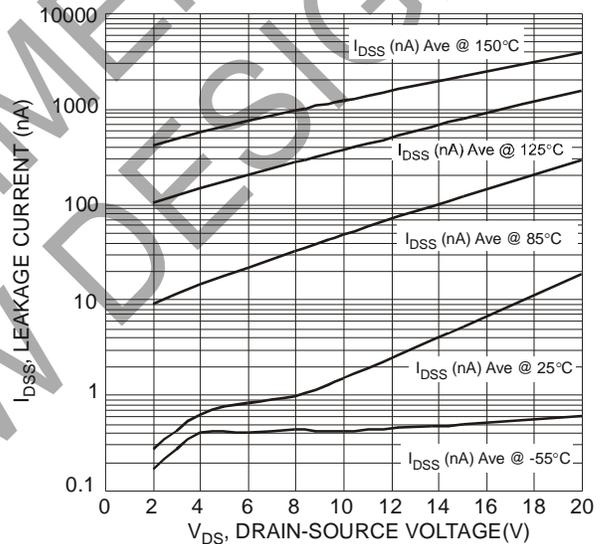


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

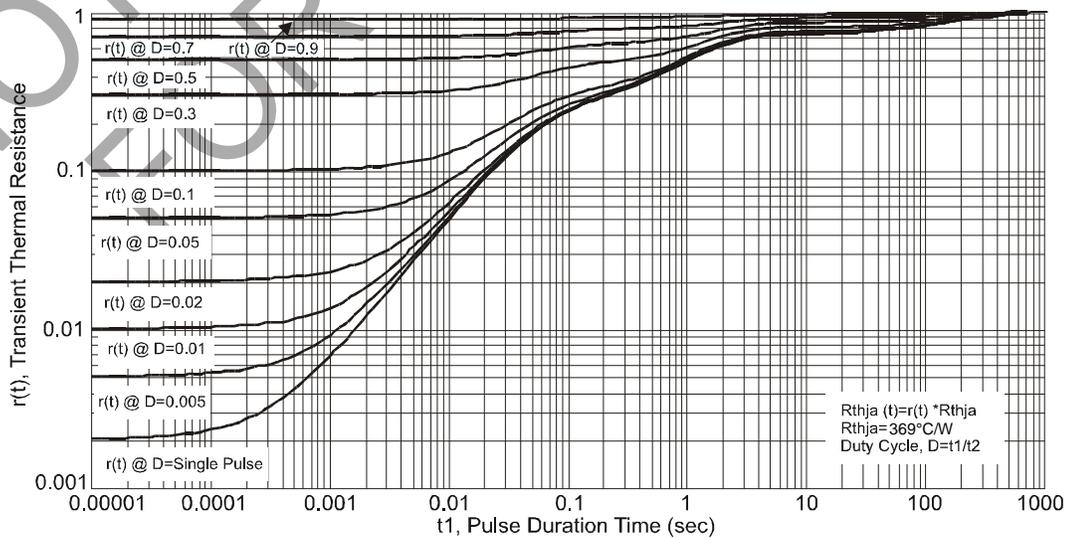
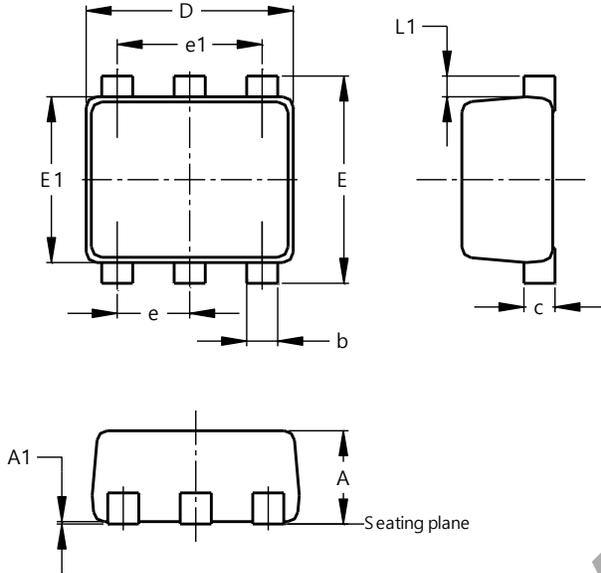


Fig. 11 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT963

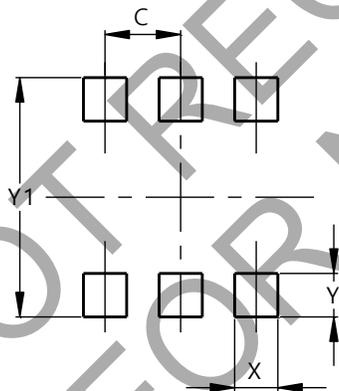


SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0.00	0.05	—
b	0.10	0.20	0.15
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
e	—	—	0.35
e1	—	—	0.70
L1	0.05	0.15	0.10
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT963



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

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